STANDARD ST.12/B

GUIDELINES FOR THE PREPARATION OF CATEGORIZED PATENT ABSTRACT

INTRODUCTION

If a particular authority wishes the abstracts submitted to it to be categorized abstracts it is recommended that it incorporate in its regulations the following guidelines for their preparation.

DEFINITION AND PURPOSE

The preparation of uniform abstracts which will enable easy scanning thereof is to a large extent facilitated by giving the abstract a categorized form. Such an abstract is intended to constitute an efficient instrument for purposes of screening in the particular technical field, especially by assisting the reader in deciding whether there is a need for consulting the patent document itself. As to the contents of the abstract, the general guidelines apply.

PRESENTATION

A categorized abstract is divided into a limited number of sections (categories), each denoted by a well-defined heading. For easy identification, a specific digit should be assigned to every heading. The abstract should contain the following categories in the sequence below:

1. Object of the invention
2. Features of the invention
3. Field of application
4. Alternative (if appropriate)
5. Example(s) and/or drawing(s) (if appropriate).

Where applicable the chemical formula characterizing the invention should appear under heading No. 2.

CATEGORIZED SAMPLE ABSTRACTS

(a) GB-Patent No. 1 321 260

1. *Object of the invention*

An improved nickel cadmium storage battery featuring better charge retention characteristics and enhanced charge acceptance capability particularly at elevated temperatures.

2. *Features of the invention*

Addition of Zn (in the form of metal or oxide) to the positive electrode or to the electrolyte or to both in a quantity in the range 1.10 – 3.50 (pref. 2.3) or 1.10 – 1.35 (pref. 1.3) times the quantity of Zn required to saturate the electrolyte. The positive electrode comprises antipolar material, pref. CdO. Extended life of this battery is given, especially where long inactive periods or on-shelf storage is required.

5. *Example*

Composition of positive electrode: 62.O% $Ni(OH)_2$; 18.6% graphite; 11,9% CdO; 4.9% Zn; 0.6% Dynel; 2.0% H_2O.
Negative electrode: 86.09% CdO; 13.38% Ni; 0.53% Dynel.

(b) US-Patent No. 3 738 882

1. *Object of the invention*

A method for polishing gallium arsenide planar surfaces to a high degree of perfection irrespective of the crystallographic orientation or conductivity type.

2. *Features of the invention*

Gallium arsenide slices are mounted on a polishing block or wheel adjacent to a polishing medium. A constant flow of alkali metal (sodium or potassium) hypochlorite and alkali metal carbonate (pref. Na or K) solution is supplied between the slices and polishing medium, providing a relative motion between GaAs surface and polishing medium. Solution must contain sufficient bicarbonate to react with any alkali hydroxide present in the alkali solution. Polishing rate is 6 to react with any alkali hydroxide present in the alkali solution. Polishing rate is 6 – 28 mils/hr. compared with 0.7 – to react with any alkali hydroxide present in the alkali solution. Polishing rate is 6 to react with any alkali hydroxide present in the alkali solution. Polishing rate is 6 - 28 mils/hr. compared with 0.7 - 2 mils/hr. of prior art. The surface is washed *in situ* using water.

3. *Field of Application*

Production of semiconductor devices such as integrated monolithic circuits and diodes.

5. *Example*

Single crystal gallium arsenide wafers (100 cristallographic orientation and chromium doped) were mounted upon a polishing wheel rotating (in polishing medium) at 60 r.p.m. and washed with water at the rate of appr. 200 cc.p.m. for 3 minutes followed by a constant flow of 50 cc.p.m. of polishing solution (0.8 N sodium hypochlorite and 0.8 N sodium carbonate). The GaAs wafers then again water washed as mentioned above.

[WIPO Standard ST.12/C follows]